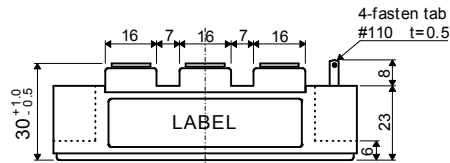
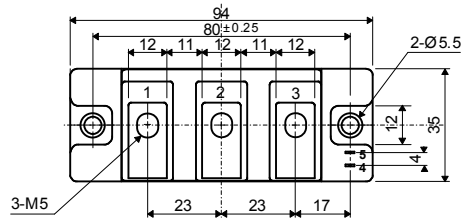
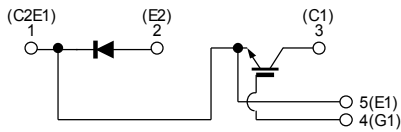


□ 回路図 : **CIRCUIT**

□ 外形寸法図 : **OUTLINE DRAWING**



Dimension: [mm]

□ **最大定格 : MAXIMUM RATINGS** (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Rated Value	Unit
コレクタ・エミッタ間電圧 Collector-Emitter Voltage	V_{CES}	600	V
ゲート・エミッタ間電圧 Gate-Emitter Voltage	V_{GES}	±20	V
コレクタ電流 Collector Current	DC	150	A
	1ms	300	
コレクタ損失 Collector Power Dissipation	P_C	560	W
接合温度 Junction Temperature Range	T_j	-40~+150	°C
保存温度 Storage Temperature Range	T_{stg}	-40~+125	°C
絶縁耐圧 (Terminal to Base AC, 1minute) Isolation Voltage	V_{iso}	2,500	V (RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink	2 (20.4)	N·m (kgf·cm)
	Busbar to Main Terminal		

□ **電気的特性 : ELECTRICAL CHARACTERISTICS** (at $T_j=25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
コレクタ遮断電流 Collector-Emitter Cut-Off Current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$	—	—	1.0	mA
ゲート漏れ電流 Gate-Emitter Leakage Current	I_{GES}	$V_{GE}=\pm 20V, V_{CE}=0V$	—	—	1.0	μA
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=150A, V_{GE}=15V$	—	2.1	2.6	V
ゲートしきい値電圧 Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=5V, I_C=150mA$	4.0	—	8.0	V
入力容量 Input Capacitance	C_{ies}	$V_{CE}=10V, V_{GE}=0V, f=1MHz$	—	7,500	—	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	$V_{CC}=300V$ $R_L=2.0\Omega$ $R_G=5.1\Omega$ $V_{GE}=\pm 15V$	—	0.15	0.30	μs
	ターンオン時間 Turn-on Time		—	0.25	0.40	
	下降時間 Fall Time		—	0.10	0.35	
	ターンオフ時間 Turn-off Time		—	0.35	0.70	

□ **フリーホイーリングダイオードの特性 : FREE WHEELING DIODE RATINGS & CHARACTERISTICS** (at $T_c=25^\circ\text{C}$) & **CHARACTERISTICS** (at $T_j=25^\circ\text{C}$)

Item	Symbol	Rated Value	Unit
順電流 Forward Current	DC	150	A
	1ms	300	

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
順電圧 Peak Forward Voltage	V_F	$I_F=150A, V_{GE}=0V$	—	1.9	2.4	V
逆回復時間 Reverse Recovery Time	t_{rr}	$I_F=150A, V_{GE}=-10V$ $di/dt=300A/\mu s$	—	0.15	0.25	μs

□ **熱的特性 : THERMAL CHARACTERISTICS**

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	IGBT	Junction to Case (T_c チップ直下での測定点)	—	—	0.22	°C/W
	Diode		—	—	0.45	

Fig.1- Output Characteristics (Typical)

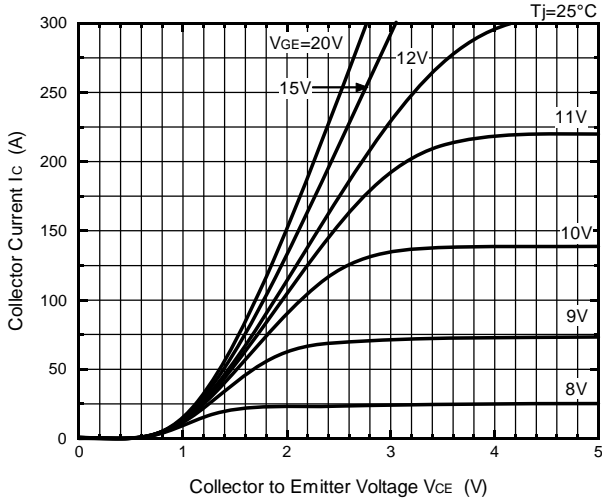


Fig.2- Output Characteristics (Typical)

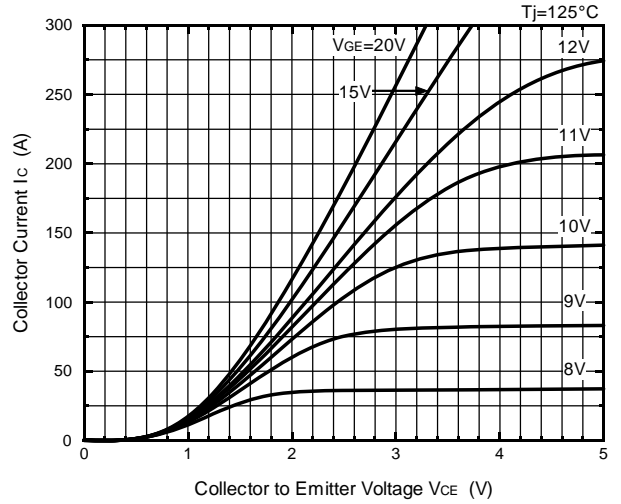


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

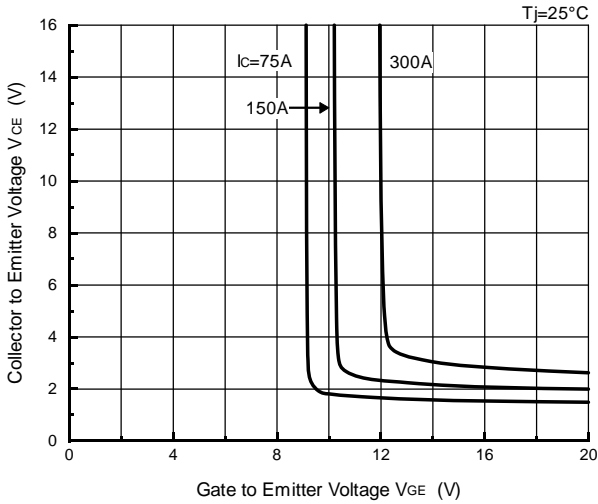


Fig.4- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

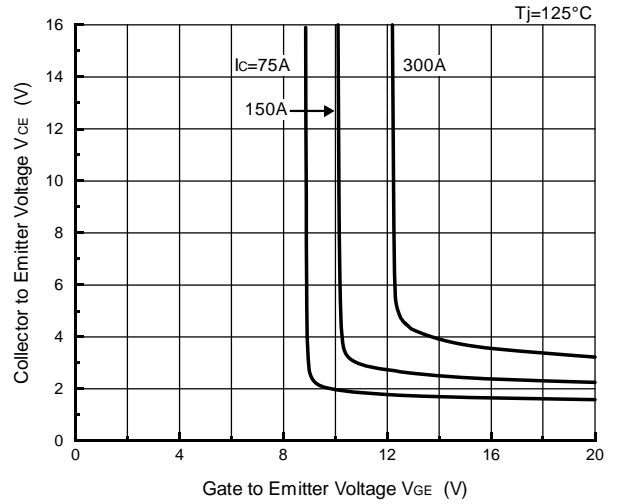


Fig.5- Gate Charge vs. Collector to Emitter Voltage (Typical)

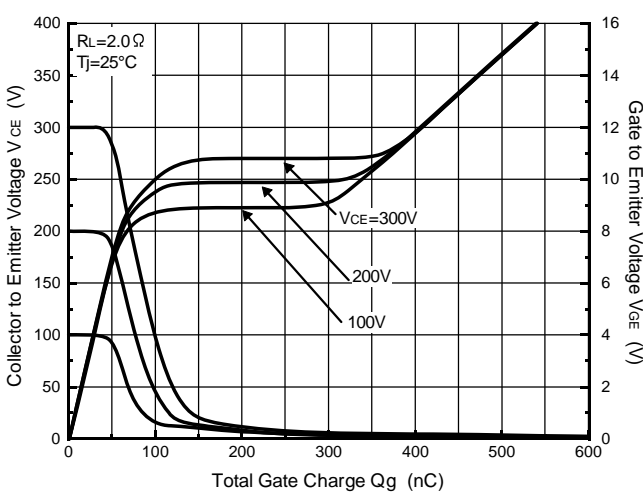


Fig.6- Capacitance vs. Collector to Emitter Voltage (Typical)

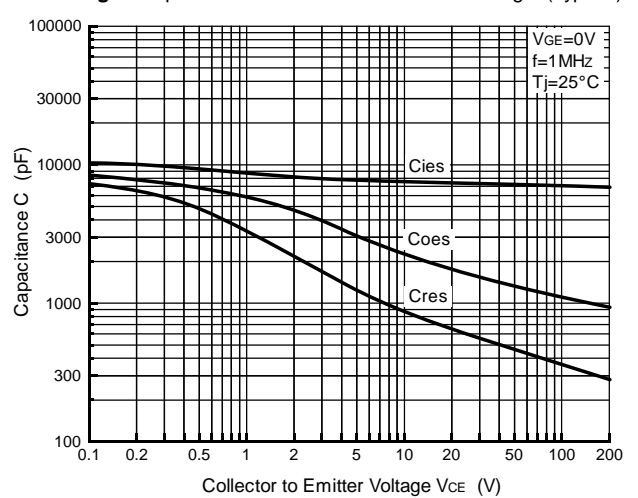


Fig.7- Collector Current vs. Switching Time (Typical)

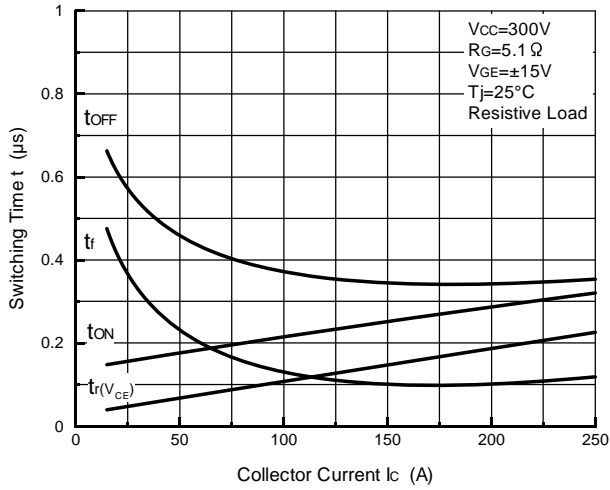


Fig.8- Series Gate Impedance vs. Switching Time (Typical)

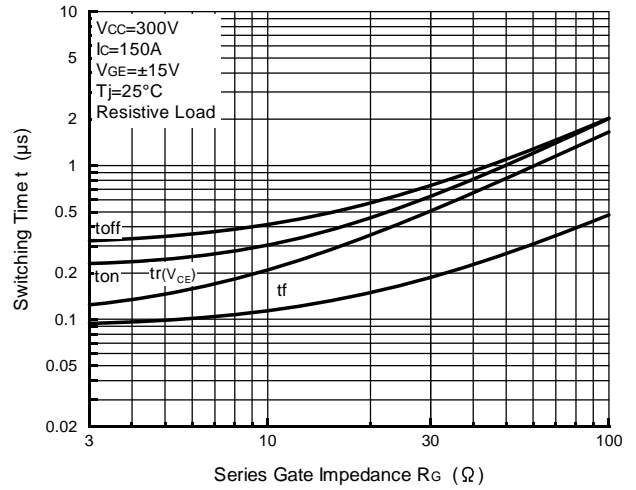


Fig.9- Collector Current vs. Switching Time

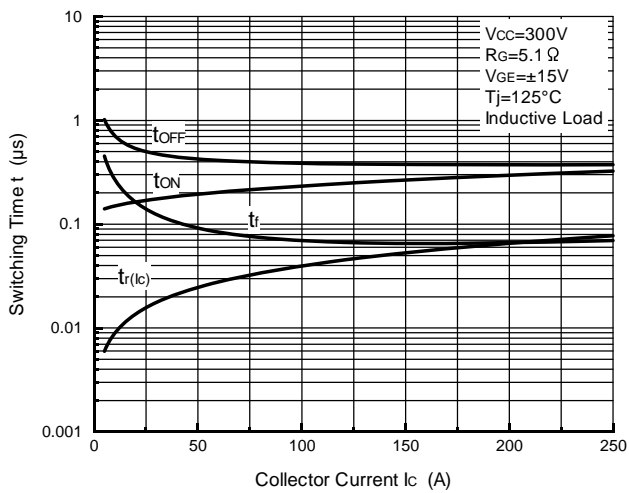


Fig.10- Series Gate Impedance vs. Switching Time

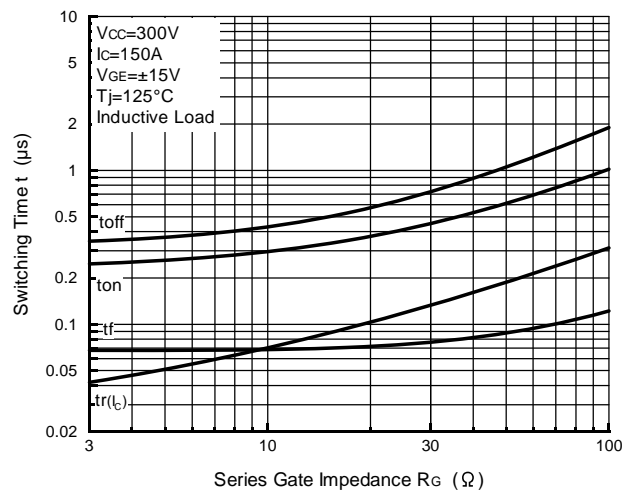


Fig.11- Collector Current vs. Switching Loss

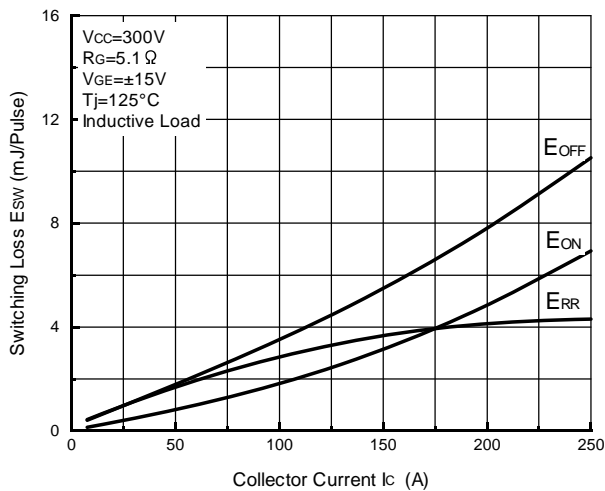


Fig.12- Series Gate Impedance vs. Switching Loss

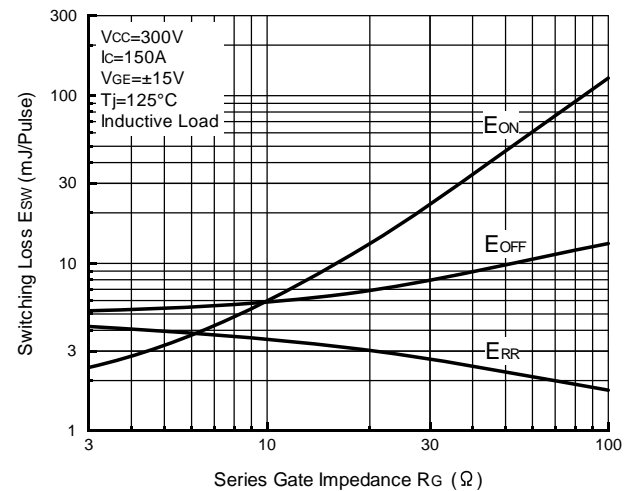


Fig.13- Forward Characteristics of Free Wheeling Diode (Typical)

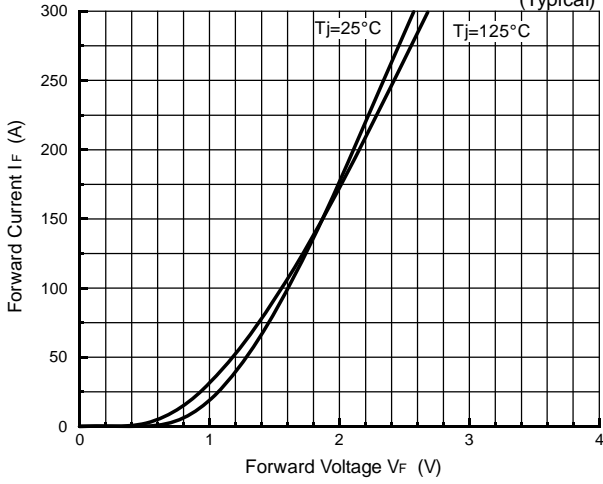


Fig.14- Reverse Recovery Characteristics (Typical)

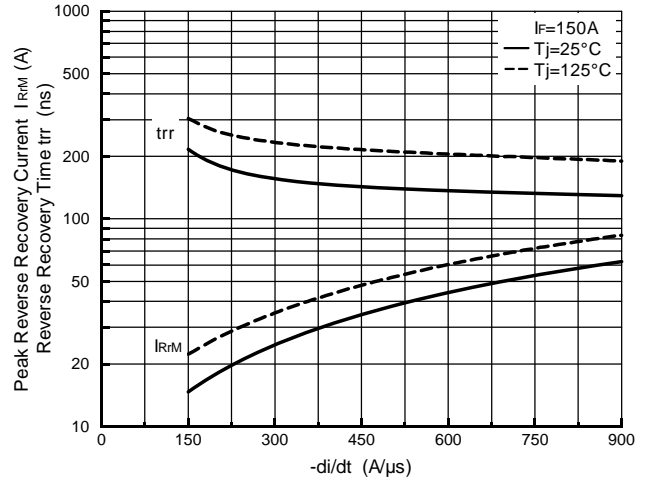


Fig.15- Reverse Bias Safe Operating Area

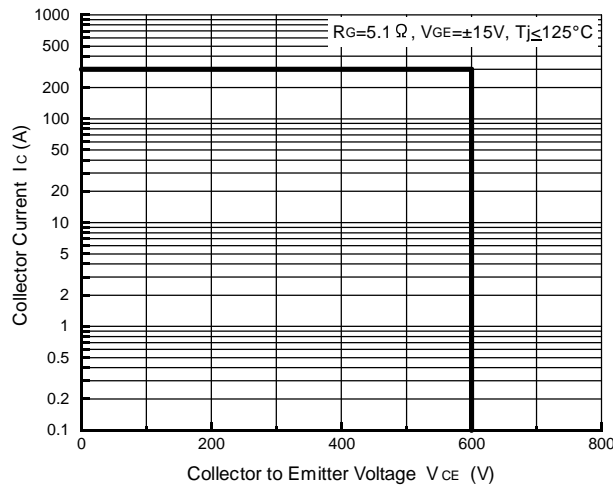


Fig.16- Transient Thermal Impedance

